

cont.
A1 10. (Amended) A nitride semiconductor device according to Claim 9, wherein said n-region multi-film layer is formed on said n-contact layer, and the total thickness of said undoped GaN layer, said n-contact layer, and said n-region multi-film layer falls within the range of 2 through $20\mu\text{m}$.

19. (Amended) A nitride semiconductor device according to Claim 18, wherein said n-region nitride semiconductor layer structure further includes an undoped GaN layer and an n-contact layer containing an n-type impurity, successively formed on said substrate.

A2 20. (Amended) A nitride semiconductor device according to Claim 19, wherein said r-region multi-film layer is formed on said n-contact layer, and the total thickness of said undoped GaN layer, said n-contact layer, and said n-region multi-film layer falls within the range of 2 through $20\mu\text{m}$.

A3 29. (Amended) A nitride semiconductor device according to Claim 26, wherein said p-type low-doped layer is made of $\text{Al}_s\text{Ga}_{1-s}\text{N}$ ($0 < s < 0.5$), and said p-type low-doped layer has a composition ratio of Al less than that of said first p-type layer.
